

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No.: 6,998,625
Issue Date: February 14, 2006
Title: Ion Implanter Having Two-Stage Deceleration Beamline
Assignee: Varian Semiconductor Equipment Associates, Inc.
Inventors: Charles M. McKenna et al.
Art Unit: 2881

WRITTEN CONSENT OF THE ASSIGNEE UNDER 37 C.F.R. § 1.324(b)(3)

Dear Sir:

As the Assignee of the above-referenced U.S. Patent No. 6,998,625, Varian Semiconductor Equipment Associates, Inc., hereby consents to the addition of **MANNY SIERADZKI** as an inventor of the same. I, **David H. Hwang, Esq., General Counsel (Acting) and Chief IP Counsel**, am authorized by Varian Semiconductor Equipment Associates, Inc. to sign on behalf of the Assignee. Also enclosed herewith is a proper statement under 37 CFR §3.73(b) establishing that Varian Semiconductor Equipment Associates, Inc. is the Assignee of the entire right, title, and interest in U.S. Patent 6,998,625.

Respectfully submitted,

Date: 8/24/07

By: _____

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